

PNP General Purpose Transistor

NST3906F3T5G

The NST3906F3T5G device is a spin-off of our popular SOT-23/SOT-323/SOT-563/SOT-963 three-leaded device. It is designed for general purpose amplifier applications and is housed in the SOT-1123 surface mount package. This device is ideal for low-power surface mount applications where board space is at a premium.

Features

- h_{FE} , 100–300
- Low $V_{CE(sat)}$, ≤ 0.4 V
- Reduces Board Space
- This is a Pb-Free Device

MAXIMUM RATINGS

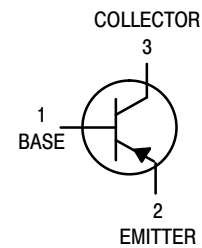
Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	–40	Vdc
Collector–Base Voltage	V_{CBO}	–40	Vdc
Emitter–Base Voltage	V_{EBO}	–5.0	Vdc
Collector Current – Continuous	I_C	–200	mAdc

THERMAL CHARACTERISTICS

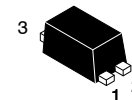
Characteristic	Symbol	Max	Unit
Total Device Dissipation, $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D (Note 1)	290 2.3	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$ (Note 1)	432	$^\circ\text{C}/\text{W}$
Total Device Dissipation, $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D (Note 2)	347 2.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$ (Note 2)	360	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction–to–Lead 3	$R_{\psi JL}$ (Note 2)	143	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	T_J, T_{stg}	–55 to +150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. 100 mm² 1 oz, copper traces.
2. 500 mm² 1 oz, copper traces.

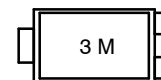


NST3906F3T5G



SOT-1123
CASE 524AA
STYLE 1

MARKING DIAGRAM



3 = Device Code
M = Date Code

ORDERING INFORMATION

Device	Package	Shipping [†]
NST3906F3T5G	SOT-1123 (Pb-Free)	8000/Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage (Note 3) ($I_C = 1.0\text{ mAdc}$, $I_B = 0$)	$V_{(BR)CEO}$	-40	–	Vdc
Collector–Base Breakdown Voltage ($I_C = 10\text{ }\mu\text{Adc}$, $I_E = 0$)	$V_{(BR)CBO}$	-40	–	Vdc
Emitter–Base Breakdown Voltage ($I_E = 10\text{ }\mu\text{Adc}$, $I_C = 0$)	$V_{(BR)EBO}$	-5.0	–	Vdc
Collector Cutoff Current ($V_{CE} = 30\text{ Vdc}$, $V_{BE} = 3.0\text{ Vdc}$)	I_{CEX}	–	-50	nAdc

ON CHARACTERISTICS (Note 3)

DC Current Gain ($I_C = -0.1\text{ mAdc}$, $V_{CE} = -1.0\text{ Vdc}$) ($I_C = -1.0\text{ mAdc}$, $V_{CE} = -1.0\text{ Vdc}$) ($I_C = -10\text{ mAdc}$, $V_{CE} = -1.0\text{ Vdc}$) ($I_C = -50\text{ mAdc}$, $V_{CE} = -1.0\text{ Vdc}$) ($I_C = -100\text{ mAdc}$, $V_{CE} = -1.0\text{ Vdc}$)	h_{FE}	60 80 100 60 30	– – 300 – –	–
Collector–Emitter Saturation Voltage ($I_C = -10\text{ mAdc}$, $I_B = -1.0\text{ mAdc}$) ($I_C = -50\text{ mAdc}$, $I_B = -5.0\text{ mAdc}$)	$V_{CE(sat)}$	– –	-0.25 -0.4	Vdc
Base–Emitter Saturation Voltage ($I_C = -10\text{ mAdc}$, $I_B = -1.0\text{ mAdc}$) ($I_C = -50\text{ mAdc}$, $I_B = -5.0\text{ mAdc}$)	$V_{BE(sat)}$	-0.65 –	-0.85 -0.95	Vdc

SMALL–SIGNAL CHARACTERISTICS

Current–Gain – Bandwidth Product ($I_C = 10\text{ mAdc}$, $V_{CE} = 20\text{ Vdc}$, $f = 100\text{ MHz}$)	f_T	250	–	MHz
Output Capacitance ($V_{CB} = -5.0\text{ V}$, $I_E = 0\text{ mA}$, $f = 1.0\text{ MHz}$)	C_{obo}	–	4.5	pF
Input Capacitance ($V_{EB} = -0.5\text{ V}$, $I_E = 0\text{ mA}$, $f = 1.0\text{ MHz}$)	C_{ibo}	–	10.0	pF
Noise Figure ($V_{CE} = -5.0\text{ Vdc}$, $I_C = -100\text{ }\mu\text{Adc}$, $R_S = 1.0\text{ k}\Omega$, $f = 1.0\text{ kHz}$)	NF	–	4.0	dB

SWITCHING CHARACTERISTICS

Delay Time ($V_{CC} = -3.0\text{ Vdc}$, $V_{BE} = 0.5\text{ Vdc}$)	t_d	–	35	ns
Rise Time ($I_C = -10\text{ mAdc}$, $I_{B1} = -1.0\text{ mAdc}$)	t_r	–	35	
Storage Time ($V_{CC} = -3.0\text{ Vdc}$, $I_C = -10\text{ mAdc}$)	t_s	–	250	ns
Fall Time ($I_{B1} = I_{B2} = -1.0\text{ mAdc}$)	t_f	–	50	

3. Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$; Duty Cycle $\leq 2.0\%$.

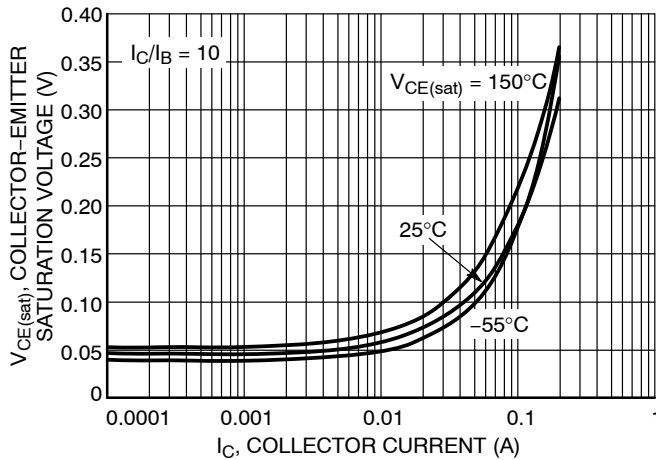


Figure 1. Collector Emitter Saturation Voltage vs. Collector Current

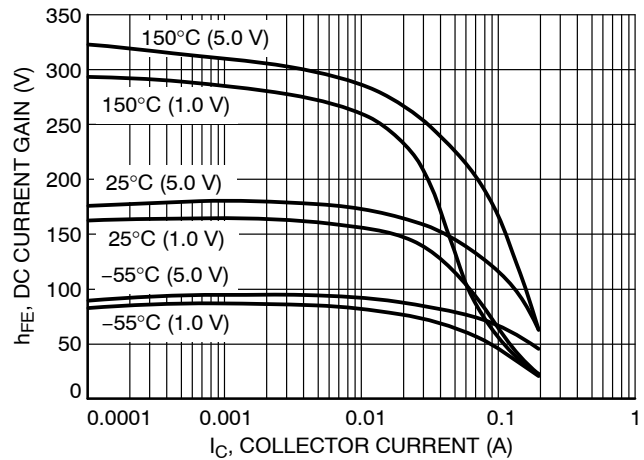


Figure 2. DC Current Gain vs. Collector Current

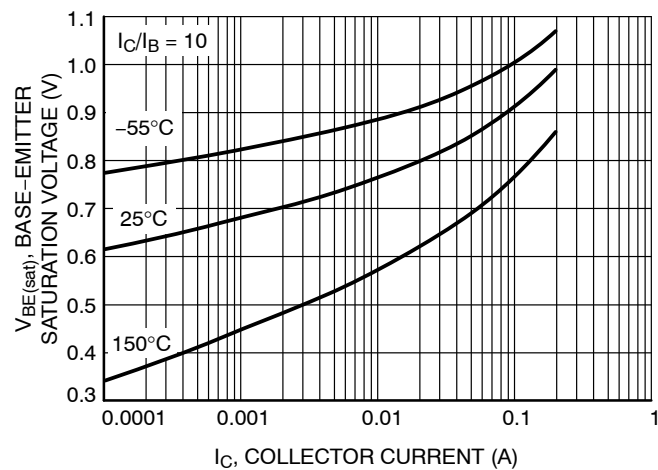


Figure 3. Base Emitter Saturation Voltage vs. Collector Current

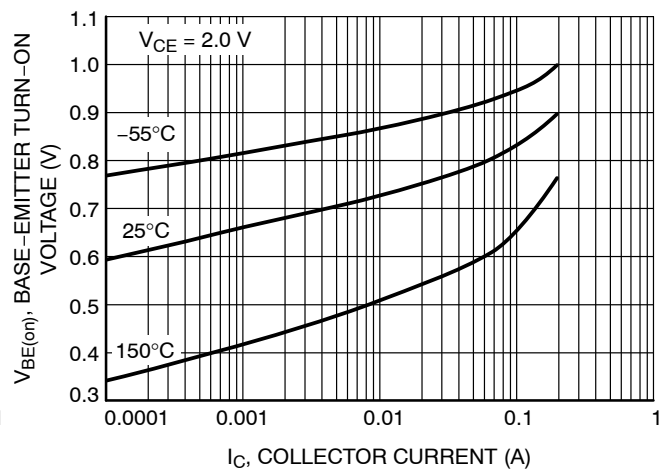


Figure 4. Base Emitter Turn-On Voltage vs. Collector Current

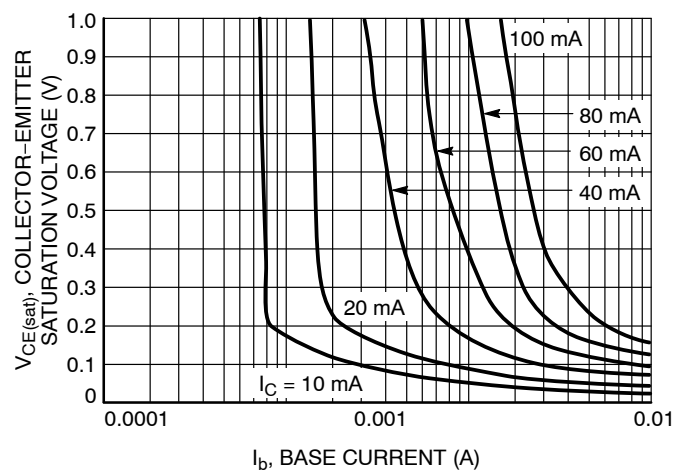


Figure 5. Saturation Region

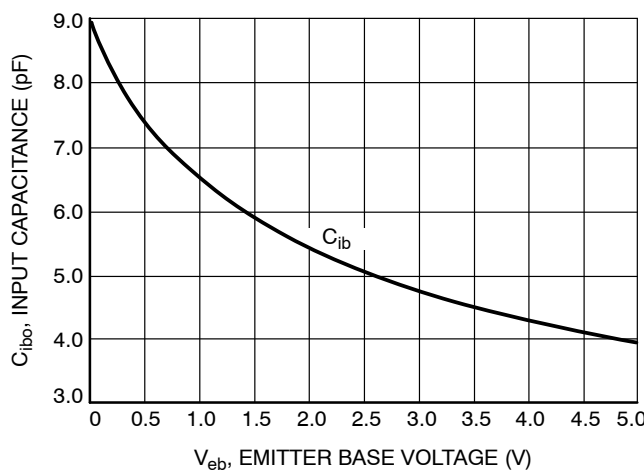


Figure 6. Input Capacitance

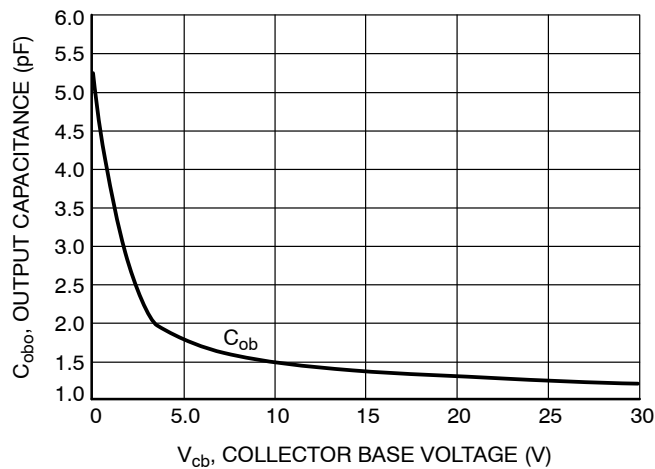
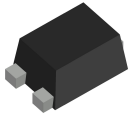
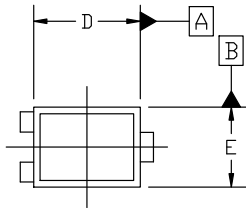


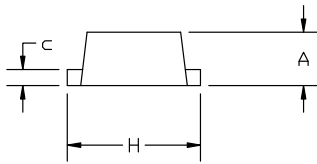
Figure 7. Output Capacitance


SOT-1123 0.80x0.60x0.37, 0.35P
CASE 524AA
ISSUE D

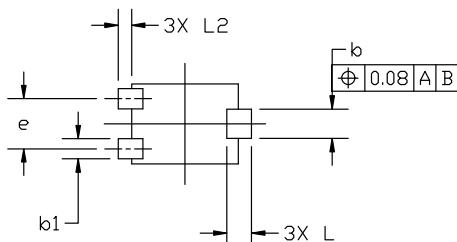
DATE 18 JAN 2024



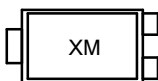
TOP VIEW



SIDE VIEW



BOTTOM VIEW

GENERIC
MARKING DIAGRAM*

X = Specific Device Code
M = Date Code

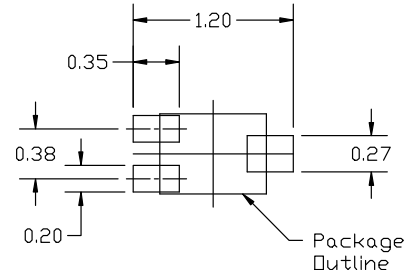
*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

MILLIMETERS

DIM	MIN	NOM	MAX
A	0.34	0.37	0.40
b	0.15	0.22	0.28
b1	0.10	0.15	0.20
c	0.07	0.12	0.17
D	0.75	0.80	0.85
E	0.55	0.60	0.65
e	0.35	0.38	0.40
H	0.950	1.000	1.050
L	0.185 REF		
L2	0.05	0.10	0.15


RECOMMENDED
MOUNTING FOOTPRINT

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference manual, SOLDERM/D.

STYLE 1:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 2:
PIN 1. ANODE
2. N/C
3. CATHODE

STYLE 3:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 5:
PIN 1. GATE
2. SOURCE
3. DRAIN

DOCUMENT NUMBER: 98AON23134D

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DESCRIPTION: SOT-1123 0.80x0.60x0.37, 0.35P

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